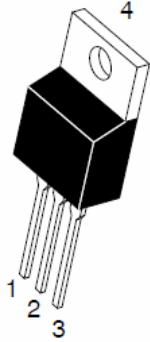
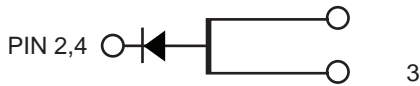


Trench MOS Barrier Schottky Rectifier

TO-220AB
TSR L10 CT-S



ITO-220AB
TSR L10 CTF-S



Features

- Advanced trench technology
- Low forward voltage drop
- Low power losses
- High efficiency operation
- Lead Free Finish, RoHS Compliant

Applications

- DC/DC Converters
- AC/DC Adaptors
- Switching Power Supplies
- Freewheeling Diodes

Maximum ratings and electrical characteristics (T_J = 25°C unless otherwise noted)

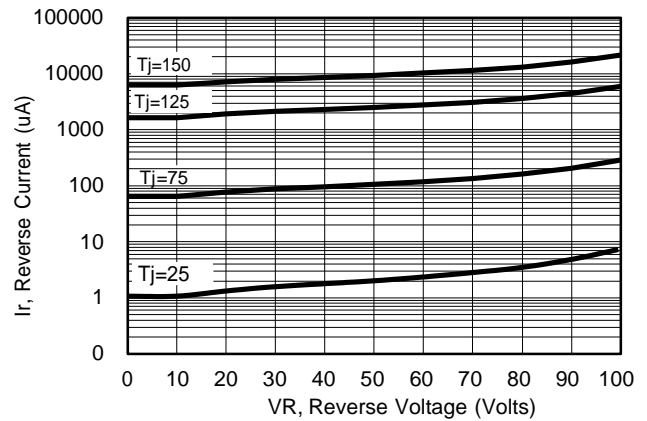
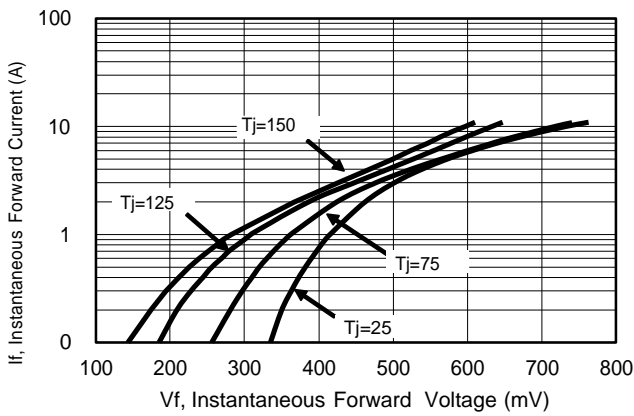
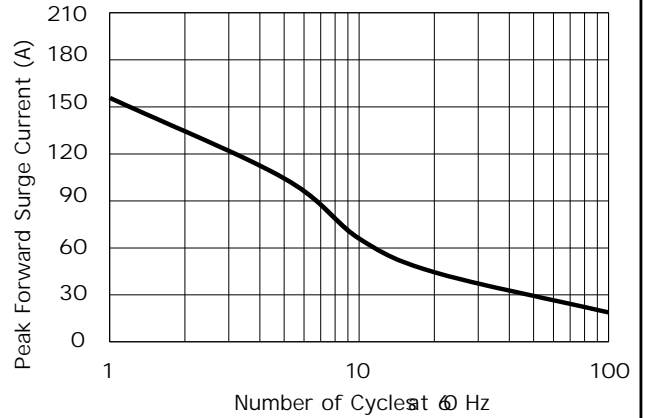
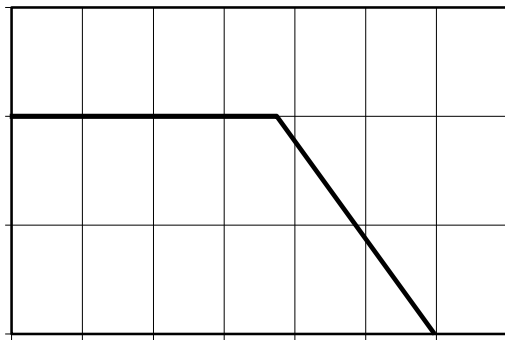
| Parameter | | Symbol | Limit | | Unit |
|---|------------|-----------|-------------|------|------|
| Maximum repetitive peak reverse voltage | | VRRM | 100 | | V |
| Maximum average forward rectified current | per device | IF(AV) | 10 | | A |
| Peak forward surge current 8.3 ms single half sine- wave superimposed on rated load per diode | | IFSM | 160 | | A |
| Operating junction and storage temperature range | | TJ, TSTG | -55 to +150 | | °C |
| Typical thermal resistance per leg | | TO-220AB | 2 | | °C/W |
| | | ITO-220AB | 4 | | °C/W |
| Instantaneous forward voltage per diode | | | TYP. | MAX. | V |
| | IF=2A | TJ=25°C | 0.44 | 0.50 | |
| | IF=2A | TJ=125°C | 0.39 | - | |
| | IF=10A | TJ=25°C | 0.63 | 0.70 | |
| Instantaneous reverse current per diode at rated reverse voltage | TJ=25°C | | - | 50 | µA |
| | TJ=125°C | | - | 10 | mA |

Notes:

(1) Pulse test: 300 µs pulse width, 1 % duty cycle

(2) Pulse test: Pulse width ≤ 40 ms

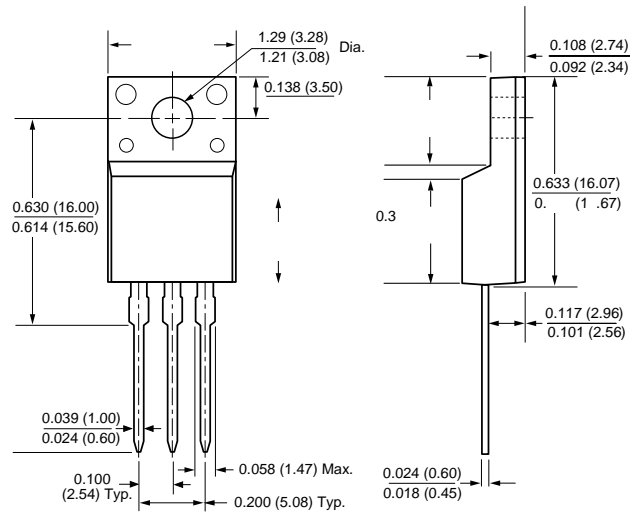
RATINGS AND CHARACTERISTICS CURVES (TA = 25 °C unless otherwise noted)



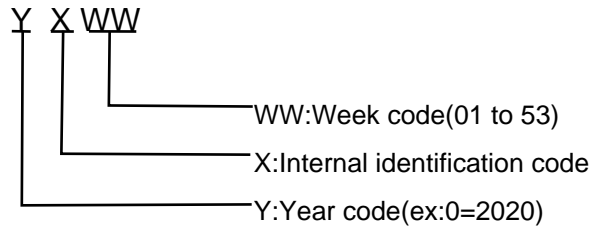
5 H Y H Q R Q H W Q J

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PACKAGE OUTLINE DIMENSIONS



- ①W : Company's trademark
- ②Product model : TSR10L100CT or TSR10L100CTF
- ③PDC information



1.Tube Dimensions

2.Inside Box

3.Outside Box

| NO | UNIT | Tube Dimensions | | Inside Box | Outside Box |
|------|------|-----------------|---|------------|-------------|
| | | A | B | | |
| Size | mm | | | | |